

Schottky Diode Gen²

$$V_{RRM} = 100\text{ V}$$

$$I_{FAV} = 2 \times 25\text{ A}$$

$$V_F = 0.72\text{ V}$$

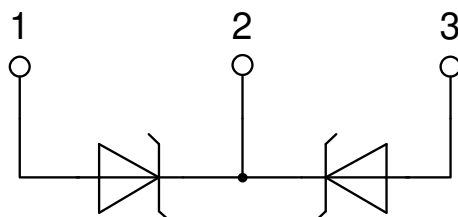
High Performance Schottky Diode
 Low Loss and Soft Recovery
 Common Cathode

Part number

DSA50C100HB



Backside: cathode



Features / Advantages:

- Very low V_f
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

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Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				100	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				100	V
I_R	reverse current, drain current	$V_R = 100\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			450	μA
		$V_R = 100\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			5	mA
V_F	forward voltage drop	$I_F = 25\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			0.90	V
		$I_F = 50\text{ A}$				1.07	V
		$I_F = 25\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			0.72	V
		$I_F = 50\text{ A}$				0.90	V
I_{FAV}	average forward current	$T_C = 155^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}\text{C}$			25	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		0.45	V
r_F	slope resistance					7.3	m Ω
R_{thJC}	thermal resistance junction to case					0.95	K/W
R_{thCH}	thermal resistance case to heatsink				0.3		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				160	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$			440	A
C_J	junction capacitance	$V_R = 12\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		289		pF

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			50	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking



Part description

D = Diode
 S = Schottky Diode
 A = low VF
 50 = Current Rating [A]
 C = Common Cathode
 100 = Reverse Voltage [V]
 HB = TO-247AD (3)

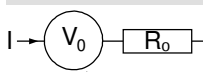
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA50C100HB	DSA50C100HB	Tube	30	502774

Similar Part	Package	Voltage class
DSA50C100QB	TO-3P (3)	100
DSA60C100PB	TO-220AB (3)	100

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}\text{C}$



Schottky

$V_{0\max}$ threshold voltage 0.45

$R_{0\max}$ slope resistance * 4.7

V

mΩ

Outlines TO-247


Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215	BSC	5.46	BSC
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242	BSC	6.14	BSC
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



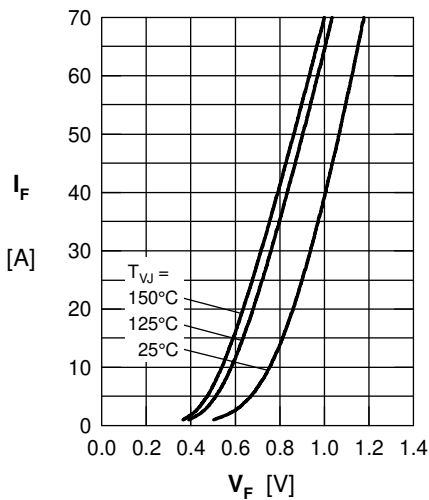
Schottky


Fig. 1 Maximum forward voltage drop characteristics

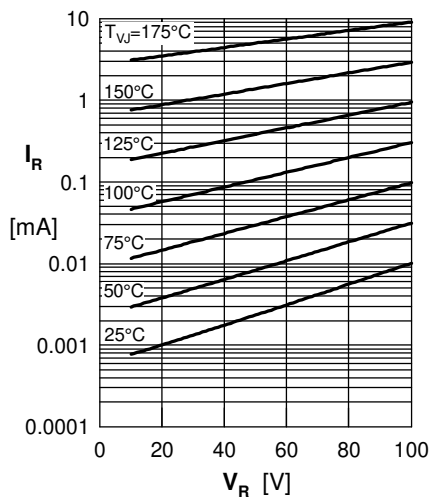


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

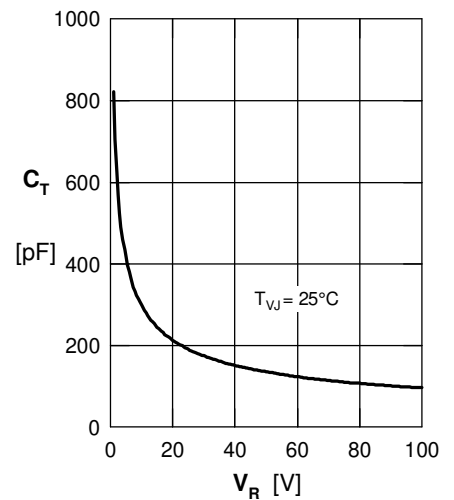


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

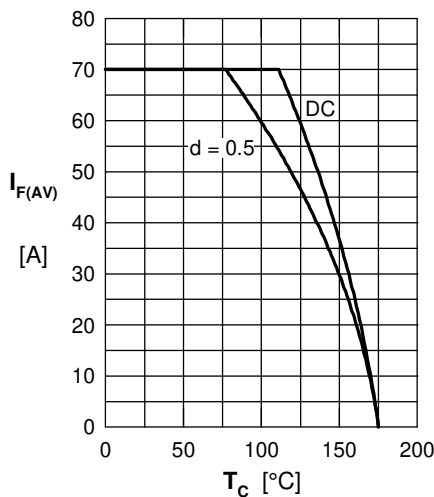


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temperature T_C

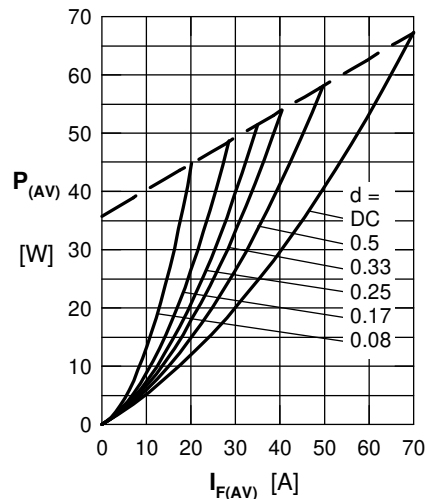


Fig. 5 Forward power loss characteristics

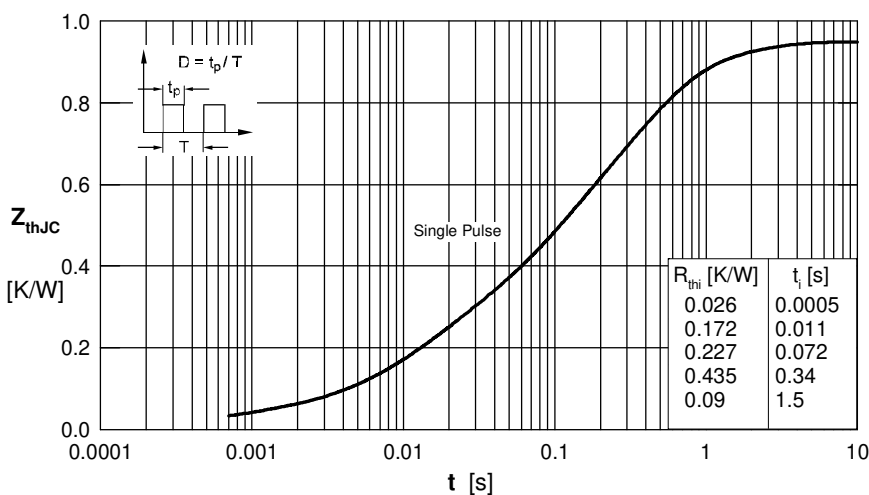


Fig. 6 Transient thermal impedance junction to case

Note: All curves are per diode